

DIGITRON SEMICONDUCTORS

1N5711, 1N5712 & 1N6263

SCHOTTKY DIODES

- For general purpose applications
- Metal-on-silicon Schottky barrier device which is protected by a PN junction guard ring.
The low forward voltage drop and fast switching make it ideal for protection of MOS devices.

MAXIMUM RATINGS @ 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Peak Inverse Voltage	1N5711	70	V
	1N6263	60	
Power Dissipation (Infinite Heatsink)	P_{tot}	400 ⁽¹⁾	mW
Maximum Single Cycle Surge 10 μ s Square Wave	I_{FSM}	2.0	A
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	0.3 ⁽¹⁾	°C/mW
Junction Temperature	T_j	125 ⁽¹⁾	°C
Storage Temperature Range	T_s	-55 to +150 ⁽¹⁾	°C

Note 1: Valid provided that leads at a distance of 4mm from case are kept at ambient temperature.

ELECTRICAL CHARACTERISTICS ($T_j = 25^\circ\text{C}$ unless otherwise noted)

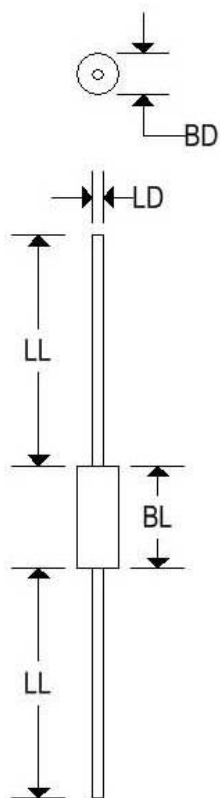
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Breakdown Voltage	1N5711	$I_R = 10\mu\text{A}$	70	-	-	V
	1N5712		20	-	-	
	1N6263		60	-	-	
Leakage Current	1N5711, 1N6263	$V_R = 50\text{V}$	-	-	200	nA
	1N5712	$V_R = 16\text{V}$	-	-	150	
Forward Voltage Drop	1N5711, 1N6263	$I_F = 1\text{mA}$	-	-	0.41	V
		$I_F = 15\text{mA}$	-	-	1.0	
		1N5712	$I_F = 35\text{mA}$	-	-	
Junction Capacitance	1N5711	$V_R = 0\text{V}, f = 1\text{MHz}$	-	-	2.0	pF
	1N5712		-	-	2.0	
	1N6263		-	-	2.2	

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MECHANICAL CHARACTERISTICS

Case:	Glass DO-35
Polarity:	Cathode Band
Marking:	Body Painted, Alpha-Numeric



	DO-35			
	Inches		Millimeters	
	Min	Max	Min	Max
BD	0.055	0.090	1.400	2.290
BL	0.120	0.200	3.050	5.080
LD	0.018	0.022	0.460	0.560
LL	1.000	1.500	25.400	38.100

Available Non-RoHS (standard) or RoHS compliant (add PBF suffix).
 Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.

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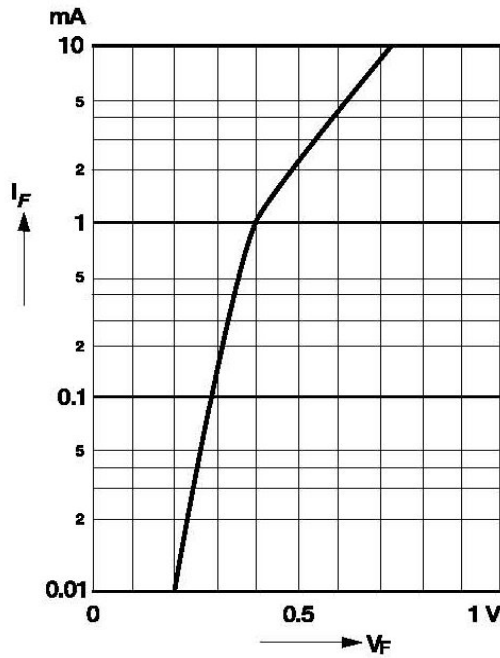
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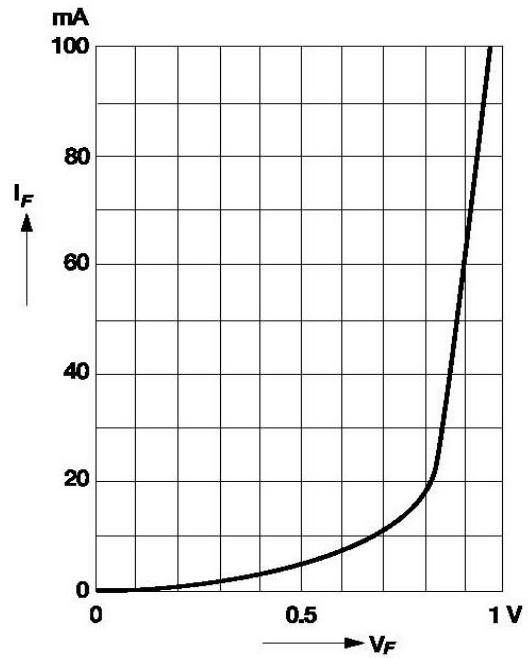
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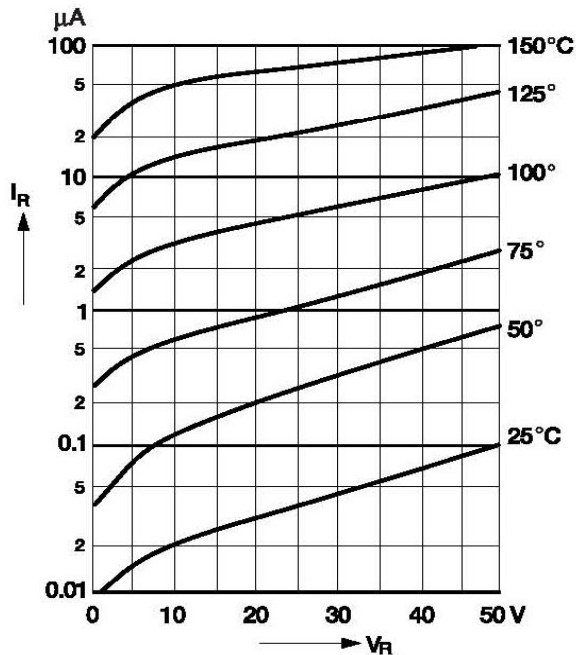
Typical variation of fwd. current vs. fwd. voltage for primary conduction through the Schottky barrier



Typical forward conduction curve of combination Schottky barrier and PN junction guard ring



Typical variation of reverse current at various temperatures



Typical capacitance curve as a function of reverse voltage

